



## 2SD1628

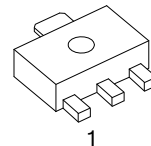
Preliminary

**NPN SILICON TRANSISTOR**

### HIGH-CURRENT SWITCHING APPLICATIONS

#### ■ FEATURES

- \* Low saturation voltage.
- \* High  $h_{FE}$ .
- \* Large current capacity.



SOT-89

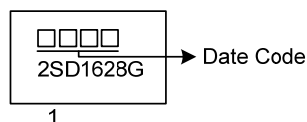
#### ■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2SD1628L-x-AB3-R	2SD1628G-x-AB3-R	SOT-89	B	C	E	Tape Reel

Note: Pin Assignment: E: Emitter B: Base C: Collector

2SD1628L-x-AB3-R	(1)Packing Type (2)Package Type (3)Rank (4)Green Package	(1) R: Tape Reel (2) AB3: SOT-89 (3) x: refer to Classification of $h_{FE1}$ (4) L: Lead Free, G: Halogen Free and Lead Free
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#### ■ MARKING



■ ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ , unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		$V_{CB0}$	60	V
Collector-Emitter Voltage		$V_{CEO}$	20	V
Emitter-Base Voltage		$V_{EBO}$	6	V
Collector Current	DC	$I_C$	5	A
	Pulse	$I_{CP}$	8	A
Collector Dissipation		$P_C$	0.5	W
Junction Temperature		$T_J$	150	$^\circ\text{C}$
Storage Temperature		$T_{STG}$	-55~+150	$^\circ\text{C}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

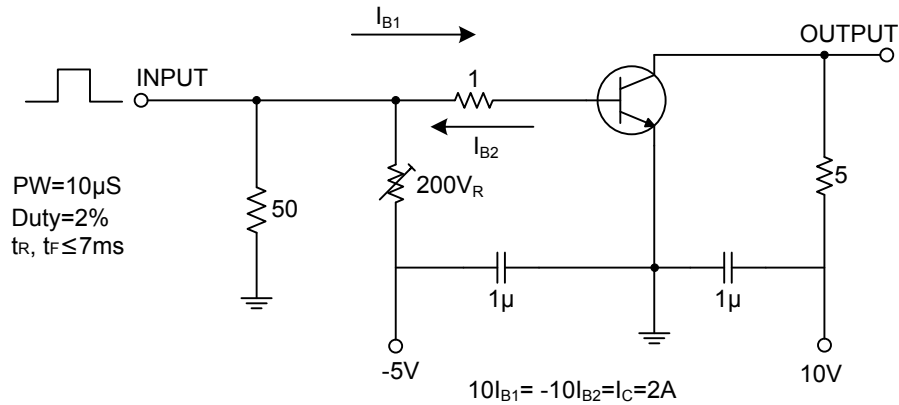
■ ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ , unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = 3\text{A}$ , $I_B = 60\text{mA}$			500	mV
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	$I_C = 3\text{A}$ , $I_B = 60\text{mA}$			1.5	V
Collector Cut-Off Current	$I_{CBO}$	$V_{CB} = 50\text{V}$ , $I_E = 0$			100	nA
Emitter Cut-Off Current	$I_{EBO}$	$V_{EB} = 5\text{V}$ , $I_C = 0$			100	nA
DC Current Gain	$h_{FE1}$	$V_{CE} = 2\text{V}$ , $I_C = 0.5\text{A}$	120		560	
	$h_{FE2}$	$V_{CE} = 2\text{V}$ , $I_C = 3\text{A}$	95			
Output Capacitance	$C_{ob}$	$V_{CB} = 10\text{V}$ , $f = 1\text{MHz}$		45		pF
Transition Frequency	$f_T$	$V_{CE} = 10\text{V}$ , $I_C = 50\text{mA}$		120		MHz
Turn On Time	$t_{ON}$	See specified Test circuit		30		ns
Storage Time	$t_S$			300		ns
Fall Time	$t_F$			40		ns

■ CLASSIFICATION OF  $h_{FE1}$

RANK	E	F	G
RANGE	120 ~ 200	160 ~ 320	280 ~ 560

■ SWITCHING TIME TEST CIRCUIT



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